

**isc Silicon NPN RF Transistor**
**2SC5084**
**DESCRIPTION**

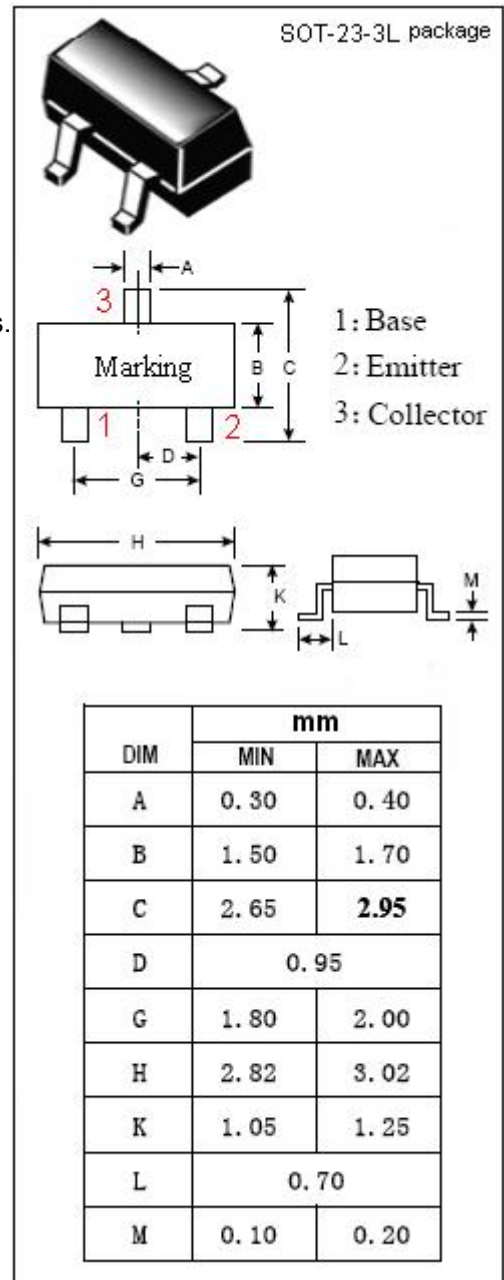
- High Gain Bandwidth Product  
 $f_T = 7 \text{ GHz TYP.}$
- High Gain, Low Noise Figure  
 $|S_{21e}|^2 = 11 \text{ dB TYP., NF} = 1.1 \text{ dB TYP @ } f = 1 \text{ GHz}$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for VHF~UHF band low noise amplifier applications.

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	20	V
V <sub>CEO</sub>	Collector-Emitter Voltage	12	V
V <sub>EBO</sub>	Emitter-Base Voltage	3	V
I <sub>C</sub>	Collector Current-Continuous	80	mA
I <sub>B</sub>	Base Current-Continuous	40	mA
P <sub>C</sub>	Collector Power Dissipation @T <sub>c</sub> =25°C	0.15	W
T <sub>J</sub>	Junction Temperature	125	°C
T <sub>stg</sub>	Storage Temperature Range	-55~125	°C



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**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 10V; I <sub>E</sub> = 0			1	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 1V; I <sub>C</sub> = 0			1	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V	80		240	
S <sub>21e</sub>   <sup>2</sup>	Insertion Power Gain	I <sub>C</sub> = 20mA;V <sub>CE</sub> = 10V; f= 500MHZ		16.5		dB
S <sub>21e</sub>   <sup>2</sup>	Insertion Power Gain	I <sub>C</sub> = 20mA;V <sub>CE</sub> = 10V; f= 1GHz	7.5	11		dB
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V	5	7		GHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f= 1.0MHz		1.0		pF
C <sub>re</sub>	Feedback Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f= 1.0MHz		0.65	1.15	pF
NF	Noise Figure	I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 10V;f= 500MHz		1		dB
NF	Noise Figure	I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 10V;f= 1GHz		1.1	2	dB

**◆ h<sub>FE</sub> Classification**

O	Y
80-160	120-240

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